# Piezochromism in the magnetic chalcogenide MnPS<sub>3</sub>

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# Abstract

van der Waals materials are exceptionally responsive to external stimuli. Pressureinduced layer sliding, metallicity, and superconductivity are fascinating examples. Inspired by opportunities in this area, we combined high pressure optical spectroscopies and first-principles calculations to reveal piezochromism in MnPS<sub>3</sub>. Dramatic color changes (green  $\rightarrow$  yellow  $\rightarrow$  red  $\rightarrow$  black) take place as the charge gap shifts across the visible regime and into the near infrared, moving systematically toward closure at a rate of approximately -50 meV/GPa and quenched only by the appearance of the insulator-metal transition. In addition to uncovering an intriguing and tunable functionality that is likely to appear in other complex chalcogenides, the discovery that piezochromism can be deterministically controlled at room temperature accelerates the development of technologies that take advantage of stress-activated modification of electronic structure.

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### INTRODUCTION

Chalcogenides are exceptionally sensitive to external stimuli. Tuning parameters like pressure and strain can alter the balance of energy scales and drive these materials into new areas of phase space where exotic properties can emerge.<sup>1-4</sup> Transition metal phosphorus trisulfides with chemical formula  $MPS_3$  (M = Mn, Ni, Fe) display a number of intriguing properties under compression including (i) insulator-metal transitions, (ii) sliding transitions, and (iii) superconductivity.<sup>5-15</sup> Another appealing aspect is pressure-induced color change [Fig. 1]. While it is not uncommon for compression to modify electronic structure, it is unusual for the response to be controllable within the visible portion of the electromagnetic spectrum.<sup>16</sup> Pressure-induced color change in the complex magnetic chalcogenide MnPS<sub>3</sub>, shown in Fig. 1, can loosely be considered as a visible analog of piezoelectricity, although the mechanisms that underlie piezochromism in complex materials 17-23 - beyond donor-acceptor complexes, polymers, and molecular systems  $^{24-34}$  - are highly under-explored.<sup>35</sup> Here, we use a combined spectroscopic and theoretical approach that builds upon recent discoveries in the MPS<sub>3</sub> family of materials<sup>5,9–11</sup> to reveal the electronic structure of MnPS<sub>3</sub> under compression, unraveling the microscopic origin of stress-activated color change, the connection of this effect to the stacking sequence, and the nature of chemical bonding in the high pressure metallic state. At the same time, we unveil a fascinating new functionality that is likely to emerge in other complex chalcogenides under pressure or strain control.

### **RESULTS AND DISCUSSION**

## Force-activated color change in $MnPS_3$

Figure 2a displays the optical response of  $MnPS_3$  as a function of pressure. At ambient conditions, the absorbance increases rapidly above 2.65 eV, in reasonable agreement with prior determinations of the direct band gap.<sup>36–39</sup> As discussed in greater detail below, the absorption edge is comprised primarily of charge transfer excitations from the 3*p* valence band of sulfur to the localized 3*d* manganese bands.<sup>36–39</sup> The literature also reveals that the spectrum contains vibronically-activated *d*-to-*d* on-site  $Mn^{2+}$  excitations at 1.92, 2.40, and 2.64 eV.<sup>36–39</sup> These features are relatively weak in our data due to optical density effects. Thus, the color properties of  $MnPS_3$  are primarily defined by the charge transfer excitations that determine the fundamental band gap. The absorption edge moves to lower energy with increasing pressure.

The band gap of  $MnPS_3$  can be extracted from the optical response using Tauc plots as:

$$\alpha(E) = \frac{A}{E} (E - E_{g,dir})^{0.5} + \frac{B}{E} (E - E_{g,ind} \mp E_{ph})^2,$$
(1)

where  $\alpha(E)$  is the absorbance,  $E_{g,dir}$  is the direct gap energy,  $E_{g,ind}$  is the indirect gap energy,  $E_{ph}$  is the mediating phonon energy, and both A and B are constants.<sup>40,41</sup> This model was originally developed for traditional semiconductors with simple single parabolic band structures. More recently, it has been extended to accommodate a variety of more complex materials.<sup>42</sup> Plots of  $[\alpha(E)]^2$  or  $[\alpha(E)]^{0.5}$  vs. energy reveal direct or indirect band gap character, respectively.<sup>40,41</sup> We carried out this analysis for MnPS<sub>3</sub> and find a 2.65 eV direct gap at ambient conditions - in excellent agreement with prior work.<sup>36–39</sup> We also find that the direct band gap of MnPS<sub>3</sub> decreases systematically from 2.65 eV at ambient conditions to 2.12 eV at 11.49 GPa [Fig. 2a,b]. In other words, it closes at the rate of -50 meV/GPa through the optical range. This trend is consistent with the images in Fig. 1.

Figure 2c displays the band gap of  $MnPS_3$  as a function of pressure. The gap traverses most of the visible range in a systematic manner. Hence, this complex chalcogenide is an agile and controllable piezochromic material with an operating range from bright green (at ambient conditions), to yellow-green (at 3 GPa), to ruby red (at 8 GPa), and to midnight black (above 20 GPa). These effects are reversible within our sensitivity. Because it has a precisely controllable piezochromic response over a wide range of the visible and into the near infrared,  $MnPS_3$  is a promising candidate for opto-electronics, spintronics, catalysis, and pressure sensor applications.<sup>6,43–45</sup>

A simple linear extrapolation of the band gap vs. pressure trend reveals two interesting energy scales. First, the gap moves outside the visible range at 20 GPa, consistent with our photographic data [Fig. 1]. Second, if the band gap were to continue closing at the same rate (-50 meV/GPa), we would anticipate full closure near 55 GPa - in reasonable agreement with theoretical predictions for the formation of metallic Mn dimers from the ambient pressure phase.<sup>11</sup> Of course, MnPS<sub>3</sub> probably undergoes a sliding transition that aligns the sulfur centers along the *c*-axis, similar to that in the Fe analog.<sup>10</sup> As discussed below, we expect that the sliding transition raises the symmetry of  $MnPS_3$  due to removal of monoclinicity by the layer stacking and that the electronic structure of this new phase collapses at much lower pressure. Consistently, our measurements reveal that the band gap drops very suddenly across the insulator-metal transition,<sup>9</sup> which we find to occur at 28.24 GPa. These events, including the development of metallicity, are shown schematically in Fig. 2d. Deterministic and promptly reversible control of the pressure-induced color change is achievable all the way from ambient conditions to the insulator-metal transition.

### Interplay between electronic and lattice effects under pressure

In order to better understand the band gap trend and insulator-metal transition, we performed complementary infrared and Raman scattering spectroscopies of  $MnPS_3$  under compression. These data allow us to examine and test the role of the lattice across the (i) sliding and (ii) insulator-metal transitions and, at the same time, reveal the development of metallicity.<sup>9-11</sup> We find two very different but highly inter-related effects. The sliding transition determines how, when, and why the band gap collapses by establishing the space group and interlayer stacking sequence from which the insulator-metal transition takes place.

We begin by examining the Raman scattering response of  $MnPS_3$  under compression. Evidence for sliding is indirect because the localized phonon modes are nearly decoupled from layer sliding. In other words, the phonons are governed by intra-slab interactions rather than inter-slab proximity effects. As a result, traditional peak coalescence due to restoration of the three-fold axes of rotation<sup>46</sup> is replaced by subtle crossover features in the phonon spectra. These small but important frequency shifts occur between 8 and 10 GPa [Fig. 3a], in agreement with our theoretical calculations that show how gradual layer sliding is made manifest in the Raman response. Full details are given in the Supplementary Materials. Interestingly, the band gap vs. pressure trend is relatively linear in this regime [Fig. 2c] - an indication that the electronic properties of MnPS<sub>3</sub> are decoupled from the sliding transition as well. This is because the charge transfer excitations that define the gap are local (rather than long-range) in nature and therefore mostly unaffected by the relative positioning of the two-dimensional chalcogenide layers. Nonetheless, the sliding transition renormalizes the critical pressure for band gap closure as discussed below. Next we consider the spectroscopic properties of  $MnPS_3$  across the insulator-metal transition.<sup>9</sup> It is important to realize that a true metal will sport free carriers and a Drude response (along with strongly screened phonons), a weak metal will show an over-damped response, and a semiconductor will reveal strong phonons riding on a low, flat electronic background. A pressure-driven insulator-to-metal transition ought, therefore, to unveil the development of a Drude response with well-screened phonons. The infrared response of  $MnPS_3$  is displayed in Fig. 3b,c. At ambient pressure, the reflectance is low and flat, with a prominent P–S stretching mode near 580 cm<sup>-1</sup>. The dashed black line guides the eye, omitting the well-known signature of the diamond anvils. These features are very consistent until the level starts to rise slightly near 26 GPa. A metallic Drude response that completely screens the aforementioned vibrational mode develops quite suddenly in our hands at 28.24 GPa. Figure 3c highlights the simultaneous disappearance of the infrared-active P–S stretching mode in the high pressure phase, consistent with the development of metallicity. The full trend is shown in Supplementary Materials.

### Expedited gap closure due to the sliding transition

In order to clarify the role of the interlayer structure in determining the rate of band gap closure, we performed first-principles density functional theory (DFT) and dynamical meanfield theory (DMFT) calculations for three different structural models: (i) the monoclinic C2/m structure at ambient conditions with a staggered phosphorous-dimer arrangement across the layers [Fig. 4a], (ii) the intermediate-pressure structure after the sliding transition with an aligned phosphorous-dimer configuration [Fig. 4b], and (iii) the high-pressure structure, similar to the aligned P-dimer phase in terms of stacking but with an aligned phosphorous-chain structure across the layers [Fig. 4c]. The lattice was fully relaxed in each case to minimize energy with the given structural (symmetry and volume) constraints; see Methods section for further details. Note that, according to a comparison of enthalpy from DFT+U calculations, the aligned P-dimer structure is almost as stable as the staggered P-dimer structure even at ambient conditions; it becomes the ground state above  $\approx 10$  GPa (see Supplementary Materials). We also expect the sliding transition to occur across a fairly broad pressure range as evidenced by the gradual change in the Raman spectra of MnPS<sub>3</sub> as well as the x-ray diffraction in  $\text{FePS}_3^{10}$ , but for simplicity we chose the staggered and aligned P-dimer and chain structures as extremal cases for this analysis.

In the ambient to small pressure range, most of the charge excitations take place within individual MnPS<sub>3</sub> layers. The absence of any sudden change in the optical band gap as a function of pressure below 20 GPa is thus attributed to the local nature of the charge transfer. As pressure is enhanced, the inter-layer distance decreases and the system starts to recognize the two different layer stackings. Because of the one-dimensional (dimerized) chain-like structure of phosphorous along the layer-normal direction in the aligned P-dimer structure [Fig. 4b], the band gap is more susceptible to pressure compared to that deriving from a staggered P-dimer structure. Eventually, collapse of the Mott-character (*i.e.* disappearance of the imaginary self-energy peak at zero energy) in the aligned P-dimer structure occurs near 45 GPa. It is accompanied by a sudden reduction of the *c*-axis spacing and an abrupt jump in the phosphorous dimer distance, which induces the one-dimensional chain-like character of phosphorous centers along the layer-normal direction [Fig. 4c]. This is discussed in the Supplementary Materials.

Figures 4d,e show the spectral functions  $A(k,\omega)$  and projected density of states  $A(\omega)$  for the aligned P-dimer state at 40.3 GPa and aligned P-chain state at 45.6 GPa, respectively. While the aligned P-dimer phase maintains Mott-insulating character [Fig. 4d], robust metallicity is observed in the aligned P-chain structure [Fig. 4e]. The appearance of dispersive band character along the layer-normal direction ( $\Gamma$ -Z line) near the Fermi level in Fig. 4d is another feature signaling the transition from a quasi-two-dimensional Mott insulating to three-dimensional metallic phase in the aligned phosphorous-chain structure of MnPS<sub>3</sub>. Note that this is in contrast to the theoretically proposed Mott transition near 64 GPa in the monoclinic staggered phosphorous dimer structure with an in-plane metallic dimerization.<sup>11</sup>

The symmetry lowering across the insulator-metal transition deserves additional comment. Our calculations reveal that the phosphorous dimer-to-chain transition  $(P\bar{3}1m$  to C2/m) takes place with a spin-state transition and Mott-type metallization. The collapse of the high-spin (S = 5/2) character leads to partial occupancy of the Mn  $t_{2g}$  orbital, which breaks the three-fold symmetry in each MnPS<sub>3</sub> layer due to the tendency towards Mn-Mn covalency. This physical picture is different than in FePS<sub>3</sub><sup>10</sup>. Here, the high-pressure metallic phase has a  $d^6$  (Fe<sup>2+</sup>) low-spin configuration and, as a consequence, prefers restoration of the three-fold symmetry. Structural responses that depend upon  $t_{2g}$  occupation have also been reported in other theoretical work<sup>11</sup>.

The precise value of the charge gap as well as the type of structural distortion that is predicted to take place across the insulator-metal transition is highly sensitive to our choice of starting structure as shown by the evolution of charge gaps of the two different stacking sequences as a function of pressure [Fig. 4f]. Use of an aligned rather than staggered P-dimer structure reduces the critical pressure from 64 GPa<sup>11</sup> to approximately 45 GPa. In view of the small energy differences between phases, we believe we are justified in identifying this with our observed insulator-metal transition. In addition to being much closer to the experimental value of the critical pressure, this model takes layer sliding into account.<sup>10</sup> Because the pressure-induced Mott transition occurs simultaneously with an abrupt separation of phosphorous dimers and restoration of the phosphorous chain structure normal to the Mn layers in the aligned P-dimer structure, it is clear that layer stacking order and inter-layer overlap between phosphorous centers is playing an important role in MnPS<sub>3</sub> under compression. Such a crucial role for phosphorous in pressurized  $MnPS_3$  is highly unexpected based upon previous studies - especially compared to the role of electron correlations and covalency in transition metal d-orbitals and chalcogen p-orbitals - in giving rise to various electronic and magnetic properties. Thus we find a clear distinction between conventional layered transition metal chalcogenides and phosphorus trisulfides, which surely deserves further investigation. At the same time, understanding of these complexities may open new avenues for control of resistivity-switching behaviors induced by uniaxial stress in this type of layered complex chalcogenide for future memory applications.

#### Structure-property relations in piezochromic materials

In order to better articulate strategies for the development of piezochromism, we compare the overall pressure scale for force-activated color change in  $MnPS_3$  with that in related materials. It is well known that chalcogenides are relatively soft and sport large volume collapses under pressure.<sup>47</sup> These and other van der Waals materials are therefore reasonable platforms to search for piezochromic effects. The nature and size of the band gap is also important. It should not be too low or too high.  $MoS_2$ , for instance, has a 1.2 eV indirect

band gap which is in the near infrared region even before compression, and it closes near 50 GPa.<sup>48,49</sup> As another example, the layered semiconductor CrSiTe<sub>3</sub> displays a 0.4 eV indirect gap and a 1.2 eV direct gap,<sup>50</sup> so it will suffer from a similar lack of dynamic range. Turning to the lead halide perovskites, systems like CH<sub>3</sub>NH<sub>3</sub>PbI<sub>3</sub> are known to sport highly-tunable electronic structures. The size of the gap at ambient conditions is on the order of 1.6 eV which is below the visible range, and it closes in a non-linear manner - resulting in a challenge for property control.<sup>51</sup> The Pb-free halide double perovskites, on the other hand, exhibit band gaps in the visible range and are therefore more promising piezochromics.<sup>52</sup> Compression also closes the 2.7 eV optical gap in  $BiFeO_3$  at a rate of -12.2 meV/GPa - with eventual metallization.<sup>53,54</sup>  $As_2S_3$  is another good example, with a 2.7 eV gap that closes rapidly.<sup>55</sup> What makes  $MnPS_3$  particularly attractive is that it has a direct band gap in the visible range.<sup>56,57</sup> With a -50 meV/GPa shift of the gap under compression, the Mn compound is both agile and linearly responsive - until metallicity develops at 28.24 GPa. Similar work on the Ni and Fe analogs will allow the development of structure-property relations. Finally, we point out that the majority of currently known piezochromics are donor-acceptor complexes, polymers, molecular systems, and liquid crystals.<sup>24? -34</sup> The development of this functionality in chalcogenides is therefore significant and potentially useful.

#### SUMMARY AND OUTLOOK

We combined diamond anvil cell techniques, optical spectroscopies, and first-principles electronic structure calculations to reveal piezochromism in the transition metal phosphorus trisulfide MnPS<sub>3</sub>. Under compression, the charge gap red-shifts across the visible and into the near infrared at a rate of -50 meV/GPa, plunging to zero at the insulator-metal transition - the upper limit of control. In addition to accelerating the discovery and fundamental understanding of stress-activated color changes in complex van der Waals materials, this striking effect is reversible and occurs at room temperature which may pave the way for interesting applications including opto-electronics, sensors, and low power memory devices.<sup>6,43–45</sup> Coverage of the full visible range and boosting sensitivity while maintaining linearity of control will advance these goals.

### **METHODS**

Crystal growth and loading the diamond anvil cell: MnPS<sub>3</sub> single crystals were prepared by chemical vapor transport techniques as described previously.<sup>58</sup> Polycrystalline material was loaded into a symmetric diamond anvil cell along with an annealed ruby ball. Care was taken to optimize the optical density in order to reveal the excitations of interest. KBr or vacuum grease were used as pressure mediums depending on the measurement. This assured a quasi-hydrostatic environment for the sample. Fluorescence from the ruby ball was used to determine pressure.<sup>59</sup>

Spectroscopic measurements: Optical measurements were performed using a Perkin Elmer Lambda-900 grating spectrometer between 1 and 6 eV with 3 nm resolution. Absorbance was calculated as  $\alpha(E) = -\ln(\mathcal{T}(E))$  where  $\mathcal{T}(E)$  is the measured transmittance. The diamond anvil cell was carefully positioned in the beam, and pressure was increased systematically. Compression was reversible within our sensitivity. We complemented the optical properties work with both infrared spectroscopy (50-8000 cm<sup>-1</sup>; 2 or 4 cm<sup>-1</sup> resolution; both transmittance and reflectance geometries) and Raman scattering ( $\lambda_{\text{excit}} = 532 \text{ nm}$ ;  $\approx 1$ mW power; 30 sec integration, averaged three times) under pressure. These experiments were performed using the 22-IR-1 beamline at the National Synchrotron Light Source II at Brookhaven National Laboratory. All data were collected at room temperature.

**First-principles calculations:** We employ the state-of-the-art embedded dynamical mean field theory (eDMFT) combined with density functional theory (DFT), which implements forces on atoms and allows relaxation of internal atomic coordinates.<sup>60</sup> For the optimization of the unit cell size and shape, we perform density functional theory calculations augmented by the on-site Coulomb repulsion U (DFT + U).<sup>61</sup> The Vienna *ab-initio* Simulation Package (VASP) is employed for the DFT + U calculations to optimize the cell shape and lattice parameters,<sup>62,63</sup> after which eDMFT optimizations of internal atomic coordinates are performed.<sup>11,60</sup> A continuous-time quantum Monte Carlo method in the hybridization-expansion limit was used to solve the auxiliary quantum impurity problem,<sup>64</sup> where the full 5 *d*-orbitals of Mn<sup>2+</sup> were chosen as our correlated subspace in a single-site DMFT approximation. Additional computational details are available in Ref.<sup>11</sup>.

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# COMPETING INTERESTS

The authors declare that there are no competing interests.

### CONTRIBUTIONS

This project was developed by JLM, KH, DV, H-SK, and NCH. crystal growth and basic characterization of the samples were carried out by AH and DM, spectroscopic measurements were performed by NCH, AJC, KRO, KAS, ZL, and JLM, and first-principles calculations were carried out by H-SK, KH, and DHV. The manuscript was written by NCH, H-SK, DHV, and JLM. All authors commented on the final document.

# DATA AVAILABILITY

Relevant data is available upon request from the corresponding author, Jan Musfeldt (email: musfeldt@utk.edu).

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FIG. 1. **Pressure-induced color change of MnPS\_3.** Photographs of piezochromic  $MnPS_3$  inside the diamond anvil cell at several characteristic pressures and also after release at room temperature.



FIG. 2. **Piezochromism of MnPS**<sub>3</sub>. **a**, Optical absorbance of MnPS<sub>3</sub> as a function of pressure. The curves are offset for clarity. **b**, Direct band gap analysis under compression. **c**, Band gap as a function of pressure. **d**, Schematic representation of the sequence of events occurring under pressure in MnPS<sub>3</sub>. Quasi-linear color control is achieved between 0 and approximately 28 GPa.



FIG. 3. Raman and infrared spectroscopy across the sliding and metal-insulator transitions in  $MnPS_3$ . a, Raman-active vibrational mode frequency under compression across the sliding transition. The gray bar denotes the crossover range. b, Infrared reflectance spectra at ambient conditions and in the metallic phase, depicting the appearance of a Drude. The dashed lines guide the eye - eliminating the diamond signature from the response. c, Close up view of the P–S stretching mode which is sharp and strong at ambient pressure and screened in the metallic state by the Drude.



FIG. 4. Theoretical structure and band gap comparison with pressure. a - c, MnPS<sub>3</sub> crystal structures with a, monoclinic (C2/m) staggered P-dimer (SPD) structure at ambient pressure, b, hexagonal  $(P\bar{3}1m)$  aligned P-dimer (APD) structure in the intermediate pressure regime  $(5 \leq P \leq 45 \text{ GPa})$ , and c, aligned P-chain (APC) structure with the monoclinic space group (C2/m). In the APD and APC structure, phosphorus ions in neighboring layers are located on top of each other, forming a chain-like structure in the APC phase above 45 GPa. d - e, k-resolved and orbital-projected spectral functions calculated with the structures shown in b, and c, respectively, showing the discontinuous nature of the APD to APC transition. f, evolution of the band gap size (obtained from DMFT) as a function of pressure, where the red and green curves represent the band gaps of the SPD and APD/APC structures, respectively. The blue dash-dotted curve shows the anticipated gap size of the APD phase between 28 and 40 GPa, where the gap closes around 30 GPa.